#### DATASHEET

# **Description**

The 9DBU0531 is a member of IDT's 1.5V Ultra-Low-Power (ULP) PCIe family. The device has 5 output enables for clock management, and 3 selectable SMBus addresses.

## **Recommended Application**

1.5V PCIe Gen1-2-3 Fanout Buffer (FOB)

## **Output Features**

• 5 1–167MHz Low-Power (LP) HCSL DIF pairs

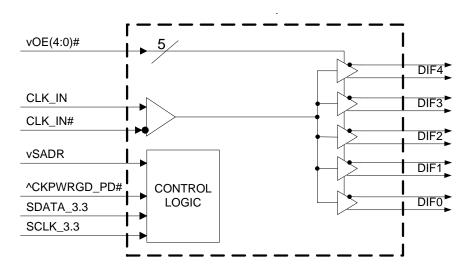
# **Key Specifications**

- DIF additive cycle-to-cycle jitter < 5ps
- DIF output-to-output skew < 60ps
- DIF additive phase jitter is < 300fs rms for PCIe Gen3
- DIF additive phase jitter < 350fs rms for SGMII

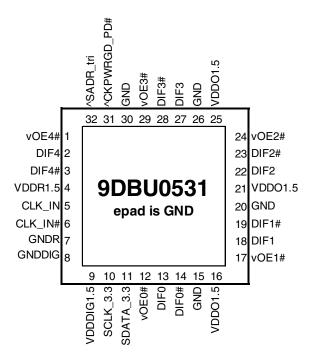
#### Features/Benefits

- LP-HCSL outputs; save 10 resistors compared to standard **HCSL** outputs
- 35mW typical power consumption; eliminates thermal concerns
- Spread Spectrum (SS) compatible; allows SS for EMI reduction
- OE# pins for each output; support DIF power management
- HCSL-compatible differential input; can be driven by common clock sources
- Spread Spectrum tolerant; allows reduction of EMI
- SMBus-selectable features; optimize signal integrity to application
  - slew rate for each output
  - · differential output amplitude
- Device contains default configuration; SMBus interface not required for device operation
- 3.3V tolerant SMBus interface works with legacy controllers
- 3 selectable SMBus addresses; multiple devices can easily share an SMBus segment
- 5 x 5 mm 32-VFQFPN; minimal board space

# **Block Diagram**



# **Pin Configuration**



#### 32-pin VFQFPN, 5x5 mm, 0.5mm pitch

^ prefix indicates internal 120KOhm pull up resistor ^v prefix indicates internal 120KOhm pull up AND pull down resistor (biased to VDD/2) v prefix indicates internal 120KOhm pull down resistor

#### **SMBus Address Selection Table**

	SADR	Address	+ Read/Write bit
State of SADR on first application of CKPWRGD_PD#	0	1101011	Х
	M	1101100	Х
	1	1101101	х

#### **Power Management Table**

CKPWRGD PD#	CLK_IN	SMBus	OEx# Pin	DIFx			
CKFWKGD_FD#	CLK_IN	OEx bit		True O/P	Comp. O/P		
0	Х	Х	X	Low	Low		
1	Running	0	X	Low	Low		
1	Running	1	0	Running	Running		
1	Running	1	1	Low	Low		

#### **Power Connections**

Pin Numb	Pin Number					
VDD	GND	Description				
4	7	Input receiver analog				
9	8	Digital power				
16, 21, 25	15,20,26,30	DIF outputs				

Note: EPAD on this device is not electrically connected to the die. It should be connected to ground for best thermal performance.

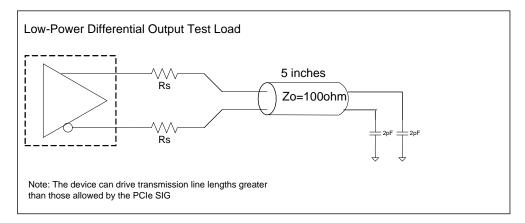


# **Pin Descriptions**

Pin#	Pin Name	Туре	Pin Description
			Active low input for enabling output 4. This pin has an internal 120kohm pull-down.
1 1	vOE4#	IN	1 = disable outputs, 0 = enable outputs.
2	DIF4	OUT	Differential true clock output.
3	DIF4#	OUT	Differential complementary clock output.
_			1.5V power for differential input clock (receiver). This VDD should be treated as an
4	VDDR1.5	PWR	Analog power rail and filtered appropriately.
5	CLK_IN	IN	True input for differential reference clock.
6	CLK_IN#	IN	Complementary input for differential reference clock.
7	GNDR	GND	Analog ground pin for the differential input (receiver)
8	GNDDIG	GND	Ground pin for digital circuitry.
9	VDDDIG1.5	PWR	1.5V digital power (dirty power)
10	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
11	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
12	vOE0#	IN	Active low input for enabling output 0. This pin has an internal 120kohm pull-down.
12	VOL0#	IIN	1 = disable outputs, 0 = enable outputs.
13	DIF0	OUT	Differential true clock output.
14	DIF0#	OUT	Differential complementary clock output.
	GND	GND	Ground pin.
16	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
17	vOE1#	IN	Active low input for enabling output 1. This pin has an internal 120kohm pull-down.
			1 = disable outputs, 0 = enable outputs.
	DIF1	OUT	Differential true clock output.
19	DIF1#	OUT	Differential complementary clock output.
	GND	GND	Ground pin.
21	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
22	DIF2	OUT	Differential true clock output.
23	DIF2#	OUT	Differential complementary clock output.
24	vOE2#	IN	Active low input for enabling output 2. This pin has an internal 120kohm pull-down.
			1 = disable outputs, 0 = enable outputs.
25	VDDO1.5	PWR	Power supply for outputs, nominally 1.5V.
26	GND	GND	Ground pin.
27	DIF3	OUT	Differential true clock output.
28	DIF3#	OUT	Differential complementary clock output.
29	vOE3#	IN	Active low input for enabling output 3. This pin has an internal 120kohm pull-down.
			1 = disable outputs, 0 = enable outputs.
30	GND	GND	Ground pin.
	101/D11/D02 22::		Input notifies device to sample latched inputs and start up on first high assertion. Low
31	^CKPWRGD_PD#	IN	enters Power Down Mode, subsequent high assertions exit Power Down Mode. This
			pin has internal 120kohm pull-up resistor.
32	^SADR_tri	LATCHED	Tri-level latch to select SMBus Address. It has an internal 120kohm pull up resistor.
	_	IN	See SMBus Address Selection Table.
33	EPAD	GND	Connect ePAD to ground.



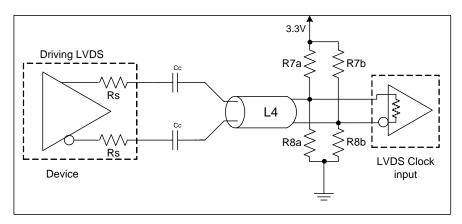
# **Test Loads**



#### **Alternate Differential Output Terminations**

Rs	Zo	Units
33	100	Ohms
27	85	Onnis

# **Driving LVDS**



#### **Driving LVDS Inputs**

	Value					
Component	Receiver has	Receiver does not				
	termination	have termination				
R7a, R7b	10K ohm	140 ohm				
R8a, R8b	5.6K ohm	75 ohm				
Cc	0.1µF	0.1µF				
Vcm	1.2 volts	1.2 volts				



# **Absolute Maximum Ratings**

Stresses above the ratings listed below can cause permanent damage to the 9DBU0531. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx	Applies to all VDD pins	-0.5		2	V	1,2
Input Voltage	$V_{IN}$		-0.5		V <sub>DD</sub> +0.5	V	1,
Input High Voltage, SMBus	$V_{IHSMB}$	SMBus clock and data pins			3.3	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD Protection	ESD prot	Human Body Model	2000			V	1

<sup>&</sup>lt;sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

# **Electrical Characteristics-Clock Input Parameters**

TA = T<sub>AMB</sub>, Supply voltages per normal operation conditions; see Test Loads for loading conditions

74057 117		, , , , , , , , , , , , , , , , , , ,					
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Input Common Mode Voltage - DIF_IN	V <sub>COM</sub>	Common mode input voltage	200		725	mV	1
Input Swing - DIF_IN	V <sub>SWING</sub>	Differential value	300		1450	mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4		8	V/ns	1,2
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = V_{DD}$ , $V_{IN} = GND$	-5		5	μΑ	
Input Duty Cycle	d <sub>tin</sub>	Measurement from differential waveform	45	50	55	%	1
Input Jitter - Cycle to Cycle	$J_{DIFIn}$	Differential measurement	0		150	ps	1

<sup>&</sup>lt;sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>&</sup>lt;sup>2</sup> Operation under these conditions is neither implied nor guaranteed.

<sup>&</sup>lt;sup>3</sup> Not to exceed 2.0V.

<sup>&</sup>lt;sup>2</sup> Slew rate measured through +/-75mV window centered around differential zero.



# **Electrical Characteristics-Input/Supply/Common Parameters-Normal Operating Conditions**

TA = T<sub>AMB</sub>; Supply voltages per normal operation conditions; see Test Loads for loading conditions

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx	Supply voltage for core and analog	1.425	1.5	1.575	V	
Ambient Operating	T <sub>AMB</sub>	Commercial range	0	25	70	°C	1
Temperature	I AMB	Industrial range	-40	25	85	°C	1
Input High Voltage	$V_{IH}$	Single-ended inputs, except SMBus	0.75 V <sub>DD</sub>		$V_{DD} + 0.3$	V	
Input Mid Voltage	$V_{IM}$	Single-ended tri-level inputs ('_tri' suffix)	$0.4~V_{DD}$		0.6 V <sub>DD</sub>	V	
Input Low Voltage	$V_{IL}$	Single-ended inputs, except SMBus	-0.3		0.25 V <sub>DD</sub>	V	
	I <sub>IN</sub>	Single-ended inputs, $V_{IN} = GND$ , $V_{IN} = VDD$	-5		5	μΑ	
Input Current	I <sub>INP</sub>	Single-ended inputs $V_{IN} = 0 \text{ V}$ ; inputs with internal pull-up resistors $V_{IN} = \text{VDD}$ ; inputs with internal pull-down resistors	-200		200	μΑ	
Input Frequency	F <sub>in</sub>		1		167	MHz	2
Pin Inductance	L <sub>pin</sub>				7	nΗ	1
	C <sub>IN</sub>	Logic Inputs, except DIF_IN	1.5		5	pF	1
Capacitance	C <sub>INDIF_IN</sub>	DIF_IN differential clock inputs	1.5		2.7	pF	1,5
	C <sub>OUT</sub>	Output pin capacitance			6	pF	1
Clk Stabilization	T <sub>STAB</sub>	From V <sub>DD</sub> power-up and after input clock stabilization or de-assertion of PD# to 1st clock			1	ms	1,2
Input SS Modulation Frequency PCIe	f <sub>MODINPCle</sub>	Allowable frequency for PCIe applications (Triangular modulation)	30		33	kHz	
Input SS Modulation Frequency non-PCIe	f <sub>MODIN</sub>	Allowable frequency for non-PCIe applications (Triangular modulation)	0		66	kHz	
OE# Latency	t <sub>LATOE#</sub>	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t <sub>DRVPD</sub>	DIF output enable after PD# de-assertion			300	μs	1,3
Tfall	$t_{F}$	Fall time of single-ended control inputs			5	ns	2
Trise	t <sub>R</sub>	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	$V_{ILSMB}$				0.6	V	
SMBus Input High Voltage	$V_{IHSMB}$	$V_{DDSMB} = 3.3V$ , see note 4 for $V_{DDSMB} < 3.3V$	2.1		3.3	V	4
SMBus Output Low Voltage	V <sub>OLSMB</sub>	at I <sub>PULLUP</sub>			0.4	V	
SMBus Sink Current	I <sub>PULLUP</sub>	at V <sub>OL</sub>	4			mA	
Nominal Bus Voltage	$V_{\text{DDSMB}}$	Bus voltage	1.425		3.6	V	
SCLK/SDATA Rise Time	t <sub>RSMB</sub>	(Max VIL - 0.15V) to (Min VIH + 0.15V)			1000	ns	1
SCLK/SDATA Fall Time	t <sub>FSMB</sub>	(Min VIH + 0.15V) to (Max VIL - 0.15V)			300	ns	1
SMBus Operating Frequency	f <sub>MAXSMB</sub>	Maximum SMBus operating frequency			400	kHz	6

<sup>&</sup>lt;sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

 $<sup>^{2}\,\</sup>mbox{Control}$  input must be monotonic from 20% to 80% of input swing.

<sup>&</sup>lt;sup>3</sup> Time from deassertion until outputs are > 200 mV.

 $<sup>^{4}</sup>$  For  $V_{DDSMB} < 3.3V$ ,  $V_{IHSMB} > = 0.8xV_{DDSMB}$ .

<sup>&</sup>lt;sup>5</sup> DIF\_IN input.

<sup>&</sup>lt;sup>6</sup> The differential input clock must be running for the SMBus to be active.



# **Electrical Characteristics-DIF Low-Power HCSL Outputs**

TA = T<sub>AMB</sub>; Supply voltages per normal operation conditions; see Test Loads for loading conditions

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Slew Rate	dV/dt	Scope averaging on, fast setting	1.4	2.3	3.5	V/ns	1,2,3
Siew Hate	dV/dt	Scope averaging on, slow setting	0.9	1.5	2.5	V/ns	1,2,3
Slew Rate Matching	∆dV/dt	Slew rate matching, scope averaging on		9.3	20	%	1,2,4
Voltage High	V <sub>HIGH</sub>	Statistical measurement on single-ended signal using oscilloscope math function. (Scope	630	750	850	mV	7
Voltage Low	$V_{LOW}$	averaging on)	-150	26	150	1114	7
Max Voltage	Vmax	Measurement on single ended signal using		763	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	22		IIIV	7
Vswing	Vswing	Scope averaging off	300	1448		mV	1,2
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	390	550	mV	1,5
Crossing Voltage (var)	Δ-Vcross	Scope averaging off		11	140	mV	1,6

<sup>&</sup>lt;sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.

# **Electrical Characteristics-Current Consumption**

 $TA = T_{AMB}$ ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
	I <sub>DDR</sub>	VDDR at 100MHz		1.84	3	mA	
Operating Supply Current	I <sub>DDDIG</sub>	VDDIG, all outputs at 100MHz		0.09	0.5	mA	
	I <sub>DDAO</sub>	VDDO1.5+VDDO, all outputs at 100MHz		21	25	mA	
	I <sub>DDRPD</sub>	VDDR, CKPWRGD_PD# = $0$		0.001	0.3	mA	2
Powerdown Current	I <sub>DDDIGPD</sub>	VDDDIG, CKPWRGD_PD# = $0$		0.1	0.2	mA	2
	I <sub>DDAOPD</sub>	VDDO1.5+VDDO, CKPWRGD_PD# = 0		0.4	1	mA	2

<sup>&</sup>lt;sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

<sup>&</sup>lt;sup>2</sup> Measured from differential waveform

<sup>&</sup>lt;sup>3</sup> Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

<sup>&</sup>lt;sup>4</sup> Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

<sup>&</sup>lt;sup>5</sup> Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

<sup>&</sup>lt;sup>6</sup> The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross\_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting Δ-Vcross to be smaller than Vcross absolute.

<sup>&</sup>lt;sup>7</sup> At default SMBus settings.

<sup>&</sup>lt;sup>2</sup> Input clock stopped.



# Electrical Characteristics-Output Duty Cycle, Jitter, Skew and PLL Characteristics

TA = T<sub>AMB</sub>; Supply voltages per normal operation conditions; see Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Duty Cycle Distortion	t <sub>DCD</sub>	Measured differentially, at 100MHz	-1	-0.2	0.5	%	1,3
Skew, Input to Output	t <sub>pdBYP</sub>	V <sub>T</sub> = 50%	2400	2862	3700	ps	1
Skew, Output to Output	t <sub>sk3</sub>	V <sub>T</sub> = 50%		30	60	ps	1,4
Jitter, Cycle to Cycle	t <sub>jcy c-cy c</sub>	Additive Jitter		0.1	5	ps	1,2

<sup>&</sup>lt;sup>1</sup> Guaranteed by design and characterization, not 100% tested in production.

#### **Electrical Characteristics-Phase Jitter Parameters**

 $TA = T_{AMB}$ ; Supply voltages per normal operation conditions; see Test Loads for loading conditions

						INDUSTRY		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	LIMIT	UNITS	Notes
	t <sub>jphPCleG1</sub>	PCIe Gen 1		0.1	5	N/A	ps (p-p)	1,2,3,5
	+	PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.1	0.4	N/A	ps (rms)	1,2,3,4, 5
	t <sub>jphPCleG2</sub>	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		0.1	0.7	N/A	ps (rms)	1,2,3,4
Additive Phase Jitter	t <sub>jphPCleG3</sub>	PCIe Gen 3 (2-4MHz or 2-5MHz, CDR = 10MHz)		0.1	0.3	N/A	ps (rms)	1,2,3,4
	t <sub>jphSGMIIM0</sub>	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		200	250	N/A	fs (rms)	1,6
	t <sub>jphSGMIIM1</sub>	125MHz, 12kHz to 20MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		313	350	N/A	fs (rms)	1,6

<sup>&</sup>lt;sup>1</sup>Guaranteed by design and characterization, not 100% tested in production.

<sup>&</sup>lt;sup>2</sup> Measured from differential waveform.

<sup>&</sup>lt;sup>3</sup> Duty cycle distortion is the difference in duty cycle between the output and the input clock.

<sup>&</sup>lt;sup>4</sup> All outputs at default slew rate.

<sup>&</sup>lt;sup>2</sup> See http://www.pcisig.com for complete specs.

<sup>&</sup>lt;sup>3</sup> Sample size of at least 100K cycles. This figure extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

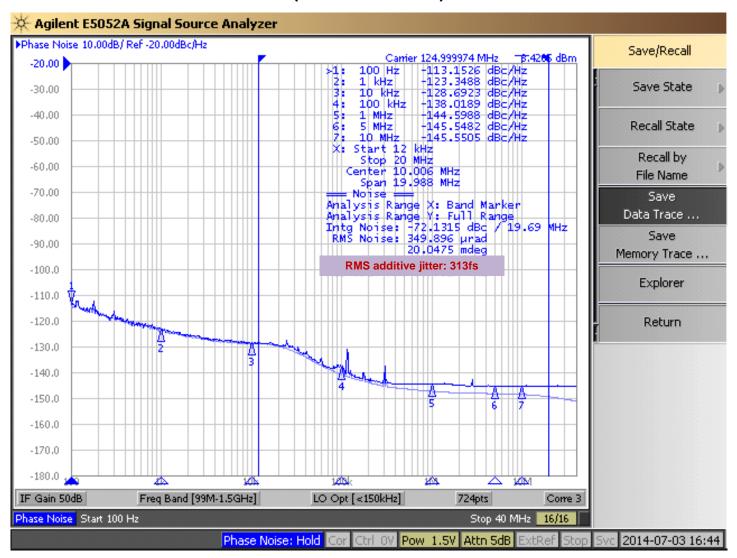
<sup>&</sup>lt;sup>4</sup> For RMS figures, additive jitter is calculated by solving the following equation: Additive jitter = SQRT[(total jitter)^2 - (input jitter)^2].

<sup>&</sup>lt;sup>5</sup> Driven by 9FGV0831 or equivalent.

<sup>&</sup>lt;sup>6</sup> Rohde & Schwarz SMA100.



# Additive Phase Jitter Plot: 125M (12kHz to 20MHz)





#### **General SMBus Serial Interface Information**

#### **How to Write**

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a stop bit

	Index Block Write Operation						
Controll	er (Host)		IDT (Slave/Receiver)				
Т	starT bit						
Slave A	Address						
WR	WRite						
			ACK				
Beginning	g Byte = N						
			ACK				
Data Byte	Count = X						
			ACK				
Beginnin	g Byte N						
			ACK				
0		×					
0		X Byte	0				
0		Ö	0				
			0				
Byte N	+ X - 1						
			ACK				
Р	stoP bit						

Note: SMBus Address is Latched on SADR pin.

#### How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X<sub>(H)</sub> was written to Byte 8)
- · Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

	peration		
Cor	ntroller (Host)		IDT (Slave/Receiver)
Т	starT bit		
SI	ave Address		
WR	WRite		
			ACK
Begi	nning Byte = N		
			ACK
RT	Repeat starT		
SI	ave Address		
RD	ReaD		
			ACK
			Data Byte Count=X
	ACK		
			Beginning Byte N
	ACK		
		ē	0
	0	X Byte	0
	0	×	0
	0		
			Byte N + X - 1
N	Not acknowledge		
Р	stoP bit		



#### SMBus Table: Output Enable Register <sup>1</sup>

Byte 0	Name	Control Function	Type	0	1	Default
Bit 7		Reserved				1
Bit 6	DIF OE3	Output Enable	RW	Low/Low	Enabled	1
Bit 5	DIF OE2	Output Enable	RW	Low/Low	Enabled	1
Bit 4		Reserved				1
Bit 3	DIF OE1	Output Enable	RW	Low/Low	Enabled	1
Bit 2		Reserved				1
Bit 1	DIF OE0 Output Enable RW Low/Low Enabled					
Bit 0		Reserved				1

<sup>1.</sup> A low on these bits will override the OE# pin and force the differential output Low/Low

#### SMBus Table: PLL Operating Mode and Output Amplitude Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				0
Bit 6		Reserved				1
Bit 5	DIF OE4	Output Enable	RW	Low/Low	Enabled	1
Bit 4		Reserved				0
Bit 3		Reserved				1
Bit 2		Reserved				1
Bit 1	AMPLITUDE 1 Controls Output Amplitude RW 00 = 0.55V 01= 0.65V					
Bit 0	AMPLITUDE 0	Controls Odtput Amplitude	RW	10 = 0.7V	11 = 0.8V	0

<sup>1.</sup> A low on the DIF OE bit will override the OE# pin and force the differential output Low/Low

#### SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function		0	1	Default
Bit 7		Reserved				1
Bit 6	SLEWRATESEL DIF3	Slew Rate Selection	RW	Slow Setting	Fast Setting	1
Bit 5	SLEWRATESEL DIF2	Slew Rate Selection	RW	Slow Setting	Fast Setting	1
Bit 4		Reserved				1
Bit 3	SLEWRATESEL DIF1	Slew Rate Selection	RW	Slow Setting	Fast Setting	1
Bit 2		Reserved				1
Bit 1	SLEWRATESEL DIFO Slew Rate Selection RW Slow Setting Fast Setting					
Bit 0		Reserved				1

Note: See "DIF 0.7V Low-Power HCSL Outputs" table for slew rates.

#### SMBus Table: DIF Slew Rate Control Register

Byte 3	Name	Control Function	Туре	0	1	Default	
Bit 7		Reserved				1	
Bit 6		Reserved				1	
Bit 5		Reserved				0	
Bit 4		Reserved				0	
Bit 3		Reserved				0	
Bit 2		Reserved					
Bit 1	Reserved					1	
Bit 0	SLEWRATESEL DIF4	Adjust Slew Rate of DIF4	RW	Slow Setting	Fast Setting	1	

Note: See "DIF 0.7V Low-Power HCSL Outputs" table for slew rates.

Byte 4 is Reserved and reads back 'hFF



#### SMBus Table: Revision and Vendor ID Register

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R			0
Bit 6	RID2	Revision ID	R	A rev = 0000		0
Bit 5	RID1	Trewsion ib	R	A rev = 0000	0	
Bit 4	RID0		R			0
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	→ 0001 = ID1/ICS		0
Bit 1	VID1	VENDORID	R			0
Bit 0	VID0		R			1

# SMBus Table: Device Type/Device ID

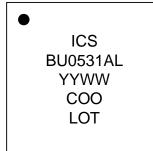
Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FGx,	01 = DBx,	1
Bit 6	Device Type0	Device Type	R	10 = DMx, $11 = DBx w/oPLL$		1
Bit 5	Device ID5		R			0
Bit 4	Device ID4		R			0
Bit 3	Device ID3	Device ID	R	000101 bina	ry or 05 hay	0
Bit 2	Device ID2	Device ID	R	000101 51114	ry or oo nex	1
Bit 1	Device ID1		R			0
Bit 0	Device ID0		R			1

# SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				0
Bit 6		Reserved				0
Bit 5		Reserved				0
Bit 4	BC4		RW			0
Bit 3	BC3		RW	Writing to this regist	er will configure how	1
Bit 2	BC2	Byte Count Programming	RW	many bytes will be r	ead back, default is	0
Bit 1	BC1		RW	= 8 b	ytes.	0
Bit 0	BC0		RW			0



# **Marking Diagrams**





#### Notes:

- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. YYWW is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.

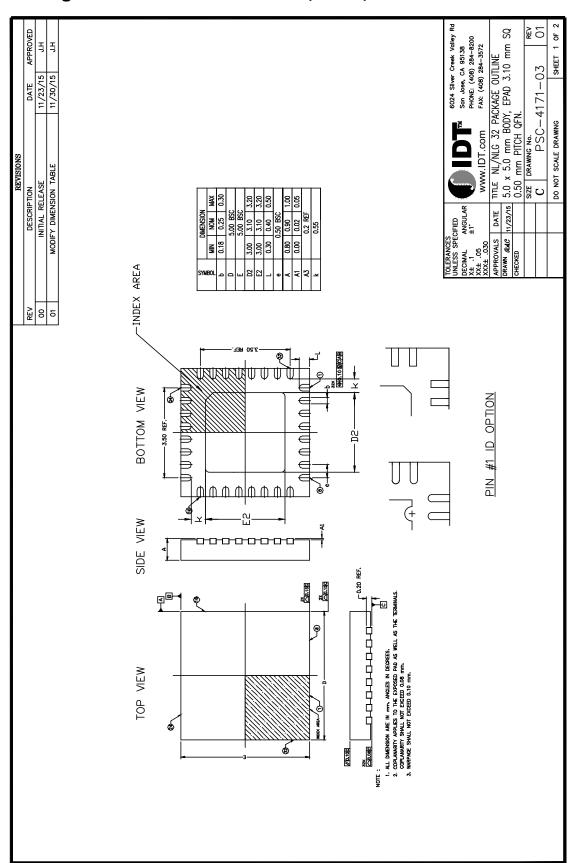
# **Thermal Characteristics**

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP VALUE	UNITS	NOTES
	$\theta_{JC}$	Junction to Case		42	°C/W	1
	$\theta_{Jb}$	Junction to Base		2.4	°C/W	1
Thermal Resistance	$\theta_{JA0}$	Junction to Air, still air	NLG32	39	°C/W	1
memai nesistance	$\theta_{JA1}$	Junction to Air, 1 m/s air flow	INLUSZ	33	°C/W	1
	$\theta_{JA3}$	Junction to Air, 3 m/s air flow		28	°C/W	1
	$\theta_{\mathrm{JA5}}$	Junction to Air, 5 m/s air flow		27	°C/W	1

<sup>&</sup>lt;sup>1</sup>ePad soldered to board

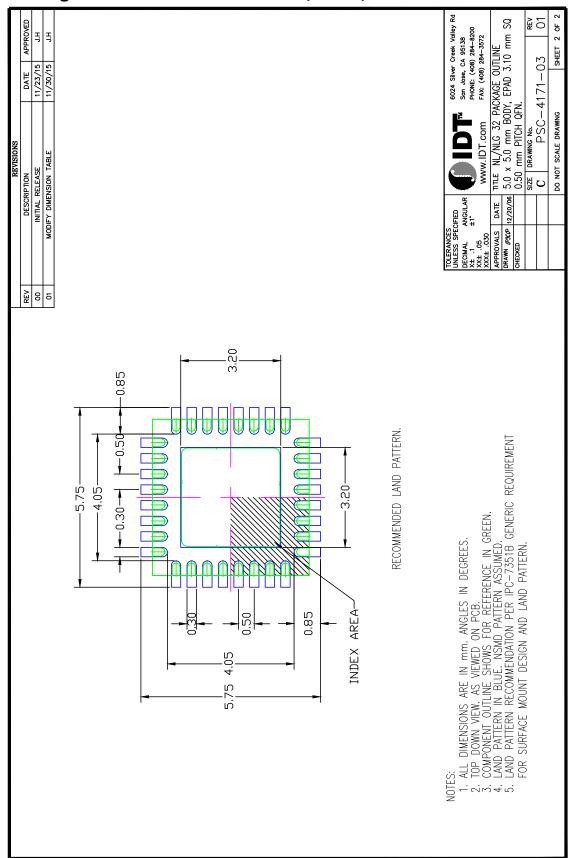


# **Package Outline and Dimensions (NLG32)**





# Package Outline and Dimensions (NLG32), cont.





# **Ordering Information**

Part / Order Number	Shipping Packaging	Package	Temperature
9DBU0531AKLF	Trays	32-pin VFQFPN	0 to +70° C
9DBU0531AKLFT	Tape and Reel	32-pin VFQFPN	0 to +70° C
9DBU0531AKILF	Trays	32-pin VFQFPN	-40 to +85° C
9DBU0531AKILFT	Tape and Reel	32-pin VFQFPN	-40 to +85° C

<sup>&</sup>quot;LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

# **Revision History**

Rev.	Initiator	Iccus Data	Description	Page #
Α	RDW	7/15/2014	,	Various
В	RDW	7/24/2014	Removed VDDIO reference in the Electrical Characteristics -	
			Input/Supply/Common Parameters and Absolute Maximum Ratings	6
			tables. This power rail does not exist on this device. The pinout and the	
			pin descriptions are correct.	
С	RDW	9/19/2014	Updated SMBus Input High/Low parameters conditions, MAX values,	6
			and footnotes.	
D	RDW	4/22/2014	Updated Key Specifications to be consistent across the family.	1-3,5
			2. Updated pin out and pin descriptions to show ePad on package	
			connected to ground.	
			3. Updated Clock Input Parameters table to be consistent with PCIe	
			Vswing parameter.	
			4. Add note about epad to Power Connections table.	
Е	RDW	2/13/2017	1. Updated pins 21 and 20 from VDDA1.5/GNDA to VDDO1.5/GND to	2.2
			clearly indicate that this part has no PLL.	2, 3
F	RDW	3/9/2017	Removed "Bypass Mode" reference in "Output Duty Cycle" and	7, 8
			"Phase Jitter Parameters" tables; update note 3 under Output Duty Cycle	
			table.	
			2. Corrected spelling errors/typos.	
			3. Change VDDA to VDDO1.5 in Current Consumption table.	
			4. Update Additive Phase Jitter conditions for PCIe Gen3.	

<sup>&</sup>quot;A" is the device revision designator (will not correlate with the datasheet revision).



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